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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
09/707,844	11/08/2000	Hidetoshi Ishida	0819-448	9493

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EXAMINER
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FARAHANI, DANA

ART UNIT	PAPER NUMBER
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2891

DATE MAILED: 09/25/2006

Please find below and/or attached an Office communication concerning this application or proceeding.



**DETAILED ACTION**

***Claim Rejections - 35 USC § 102***

1. The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless –

(b) the invention was patented or described in a printed publication in this or a foreign country or in public use or on sale in this country, more than one year prior to the date of application for patent in the United States.

2. Claims 11-14, 17 and 18 are rejected under 35 U.S.C. 102(b) as being anticipated by Inoue (US Patent 5,151,770), previously cited.

Regarding claims 11, 14, 17 and 18, Inoue discloses in figure 1, a semiconductor device comprising:

A plurality of semiconductor elements, 24 and 26, formed on a semiconductor substrate 21, 27; and

A plurality of through holes, which are provided between two adjacent ones of the plurality of semiconductor elements and pass from a surface through the backside of the semiconductor substrate, which is GaAs (see figure 5, and col. 9, lines 29-32); and

a distance between two adjacent ones of the plurality of through holes (which is 100 microns. See col. 6, line 13) is smaller than a thickness of the semiconductor substrate (which is 500 mu plus the thickness of 21).

Regarding claim 12, the through holes are covered with a conductive material (see col. 8, lines 1-5).

Regarding claim 13, the conductive material is electrically connected to a ground wiring layer 52 (figs. 4 and 5) provided on the surface of the backside of the substrate (see col. 8, lines 1-5).

3. Claims 15 and 16 are rejected under 35 U.S.C. 103(a) as being unpatentable over Inoue as applied to claims 11-14 above, and further in view of Nakamura et al., hereinafter Nakamura (US Patent 6,229,209), previously cited.

Inoue discloses the limitations in the claims, as discussed above, except for a second group of through holes which are provided in electrodes of the plurality of semiconductor elements, pass from a surface through the backside of the substrate, and whose faces are covered with conductive material.

Nakamura discloses in figure 1, a second group of through holes 23 which are provided in electrodes of the semiconductor element 3, pass from a surface through the backside of the substrate 20, and whose faces are covered with conductive material 24 (see col. 6, lines 4-19). Therefore, it would have been obvious to one of ordinary skill in the art at the time of the invention to make connection to the semiconductor devices of the Inoue in the fashion of the Nakamura reference (which would lead to their connection to the backside ground wiring 52), commonly known as flip chip structure, in order to make contacts to the semiconductor components of the Inoue, and provide a ground voltage reference for those devices. Flip chip configurations and their advantages, such as occupying less space and making secure contacts are well known in the art.

***Response to Arguments***

4. Applicant's arguments with respect to the previously rejected claims have been considered but are moot in view of the new ground(s) of rejection.

***Conclusion***

5. **THIS ACTION IS MADE FINAL.** Applicant is reminded of the extension of time policy as set forth in 37 CFR 1.136(a).

A shortened statutory period for reply to this final action is set to expire THREE MONTHS from the mailing date of this action. In the event a first reply is filed within TWO MONTHS of the mailing date of this final action and the advisory action is not mailed until after the end of the THREE-MONTH shortened statutory period, then the shortened statutory period will expire on the date the advisory action is mailed, and any extension fee pursuant to 37 CFR 1.136(a) will be calculated from the mailing date of the advisory action. In no event, however, will the statutory period for reply expire later than SIX MONTHS from the mailing date of this final action.

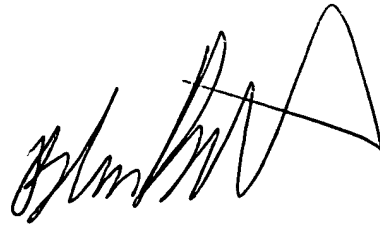
Any inquiry concerning this communication or earlier communications from the examiner should be directed to Dana Farahani whose telephone number is (571)272-1706. The examiner can normally be reached on M-F 9:00AM - 5:00PM.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Bill Baumeister can be reached on (571)272-1722. The fax phone number for the organization where this application or proceeding is assigned is 571-273-8300.

Art Unit: 2891

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see <http://pair-direct.uspto.gov>. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

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A handwritten signature in black ink, appearing to read 'B. William Baumeister', with a large, stylized flourish extending from the end of the signature.

**B. WILLIAM BAUMEISTER**  
**SUPERVISORY PATENT EXAMINER**